



STY100NS20FD

N-CHANNEL 200V - 0.022Ω - 100A Max247

MESH OVERLAY™ Power MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STY100NS20FD	200V	< 0.024Ω	100 A

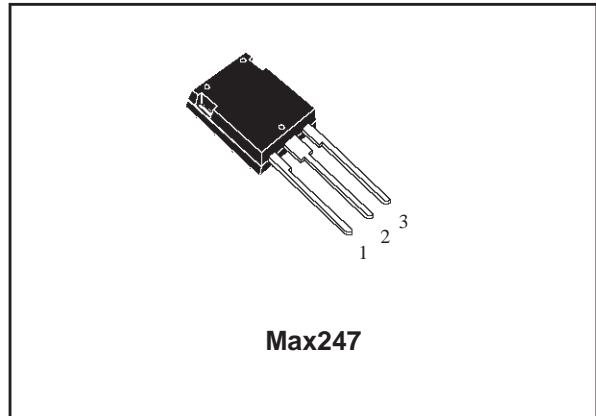
- TYPICAL R_{DS(on)} = 0.022Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- ± 20V GATE TO SOURCE VOLTAGE RATING
- LOW INTRINSIC CAPACITANCE
- FAST BODY-DRAIN DIODE: LOW t_{rr}, Q_{rr}

DESCRIPTION

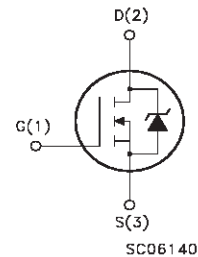
Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patented STrip layout coupled with the Company's proprietary edge termination structure, gives the lowest R_{DS(ON)} per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLY (SMPS)
- DC-AC CONVERTER FOR WELDING EQUIPMENT AND UNINTERRUPTABLE POWER SUPPLY AND MOTOR DRIVE



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	200	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	200	V
V _{GS}	Gate- source Voltage	±20	V
I _D	Drain Current (continuous) at T _C = 25°C	100	A
I _D	Drain Current (continuous) at T _C = 100°C	63	A
I _{DM} (i)	Drain Current (pulsed)	400	A
P _{TOT}	Total Dissipation at T _C = 25°C	450	W
	Derating Factor	3.6	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	25	V/ns
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(*)Pulse width limited by safe operating area

(1) I_{SD} ≤ 100A, di/dt ≤ 200A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

STY100NS20FD

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	0.277	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	30	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	100	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	750	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	200			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			10 100	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 50A		0.022	0.024	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 50A		30		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		7900		pF
C _{oss}	Output Capacitance			1500		pF
C _{rss}	Reverse Transfer Capacitance			460		pF

Note: 1. Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.

ELECTRICAL CHARACTERISTICS (CONTINUED)
SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 100V, I_D = 50A$		42		ns
t_r	Rise Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		140		ns
Q_g	Total Gate Charge	$V_{DD} = 100V, I_D = 100A,$ $V_{GS} = 10V$		360		nC
Q_{gs}	Gate-Source Charge			35		nC
Q_{gd}	Gate-Drain Charge			135		nC

SWITCHING OFF

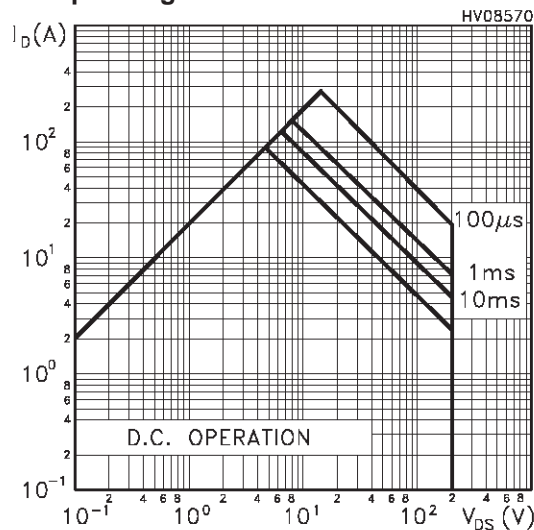
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 100V, I_D = 100A,$		245		ns
t_f	Fall Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 5)		140		ns
t_c	Cross-over Time			220		ns

SOURCE DRAIN DIODE

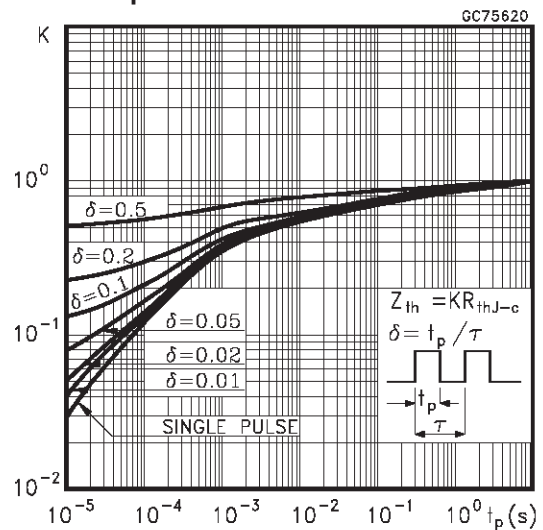
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				100	A
$I_{SDM} (2)$	Source-drain Current (pulsed)				400	A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 100A, V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 100A, di/dt = 100A/\mu s,$ $V_{DD} = 160V, T_j = 150^\circ C$ (see test circuit, Figure 5)		225		ns
Q_{rr}	Reverse Recovery Charge			1.35		μC
I_{RRM}	Reverse Recovery Current			12		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

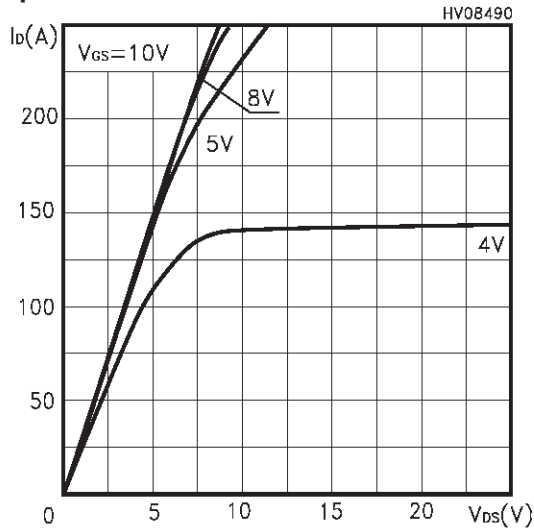
Safe Operating Area



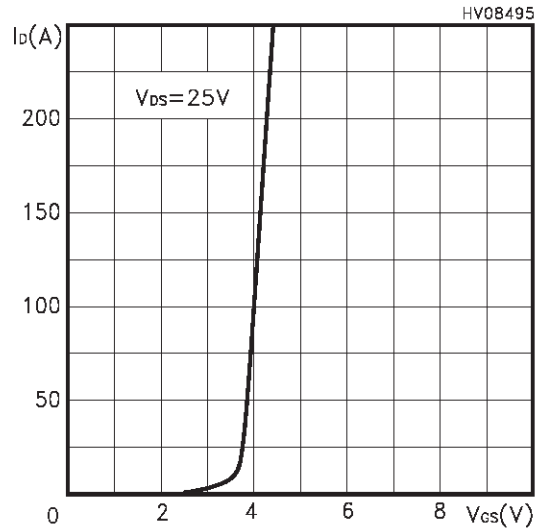
Thermal Impedance



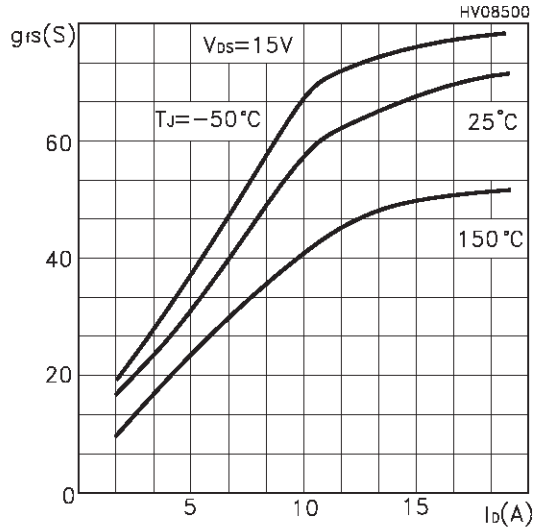
Output Characteristics



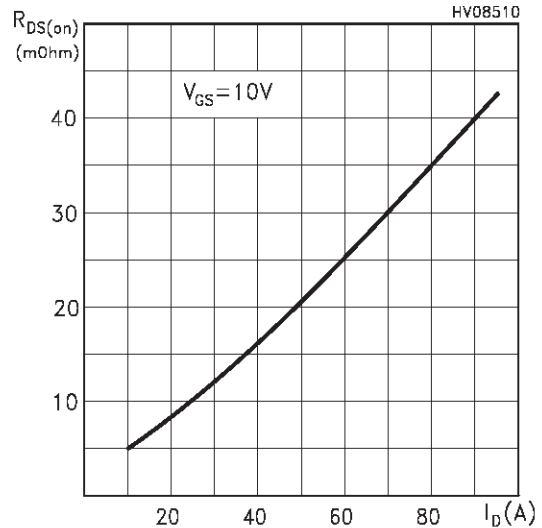
Transfer Characteristics



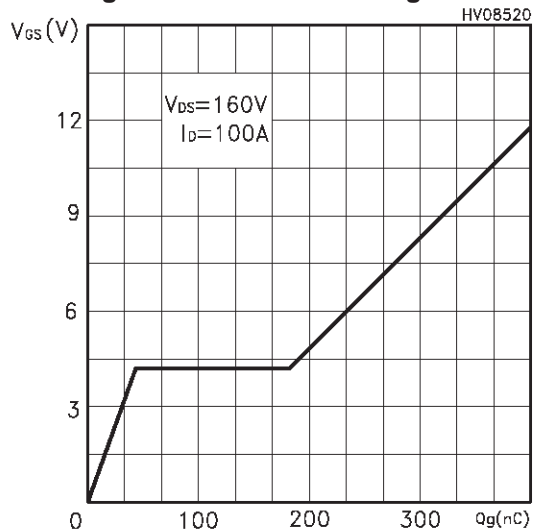
Transconductance



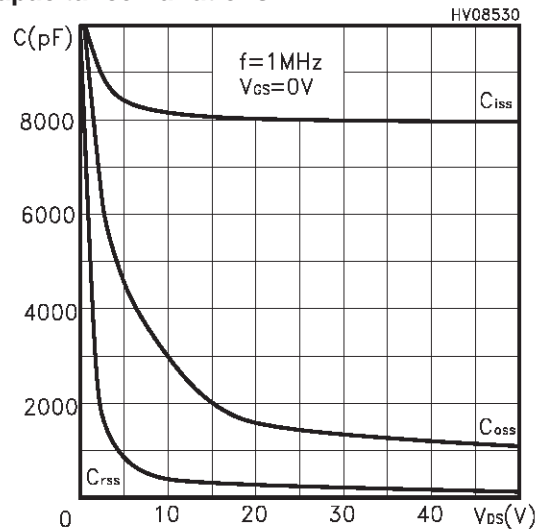
Static Drain-source On Resistance



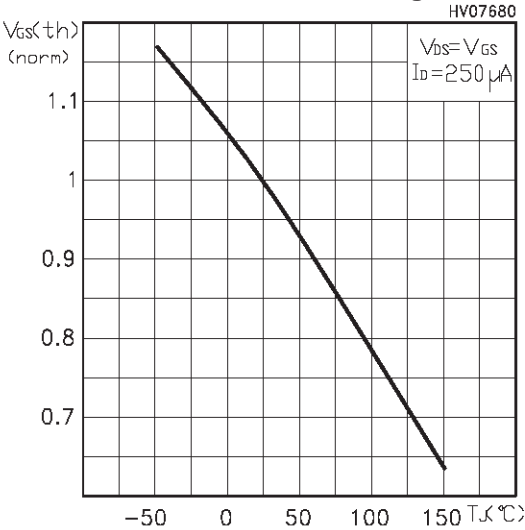
Gate Charge vs Gate-source Voltage



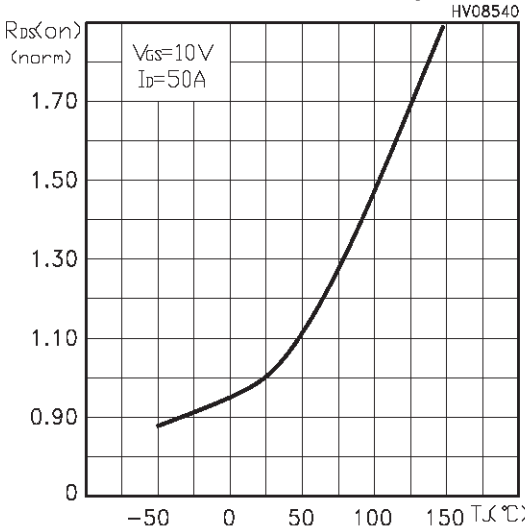
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

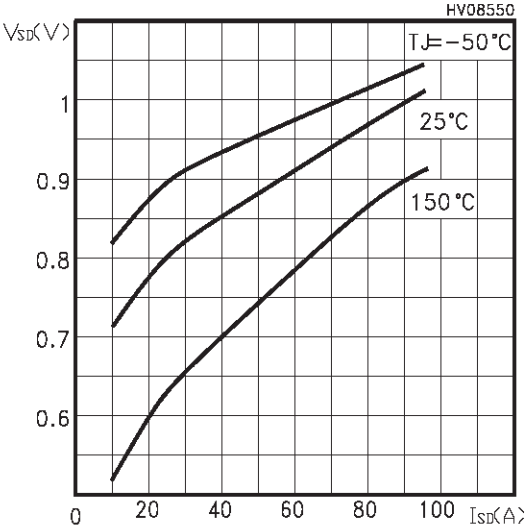


Fig. 1: Unclamped Inductive Load Test Circuit

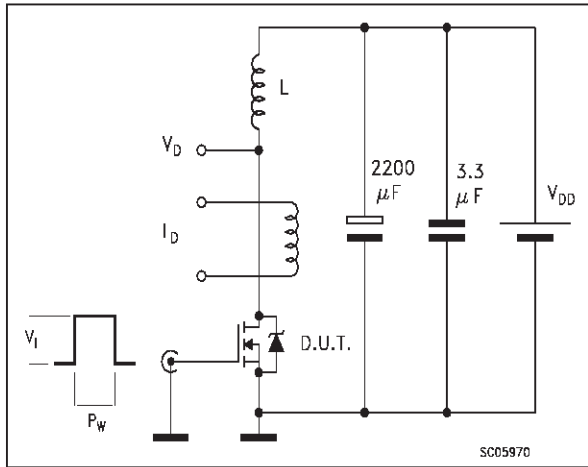


Fig. 2: Unclamped Inductive Waveform

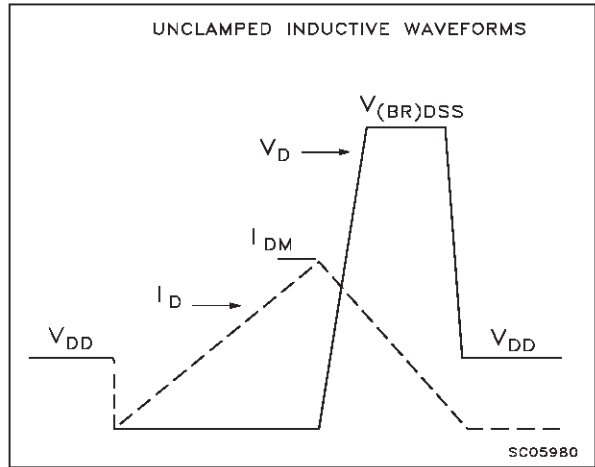


Fig. 3: Switching Times Test Circuit For Resistive Load

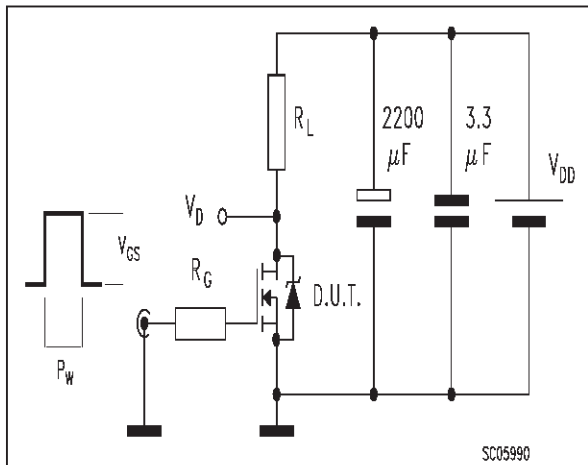


Fig. 4: Gate Charge test Circuit

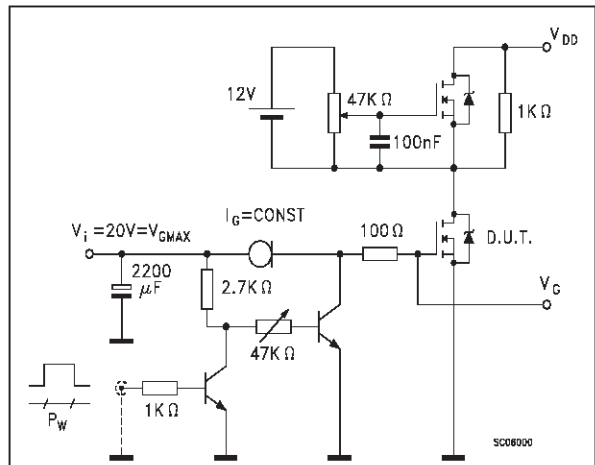
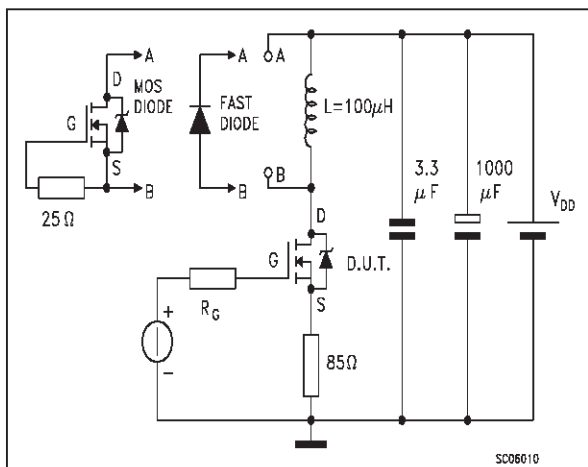
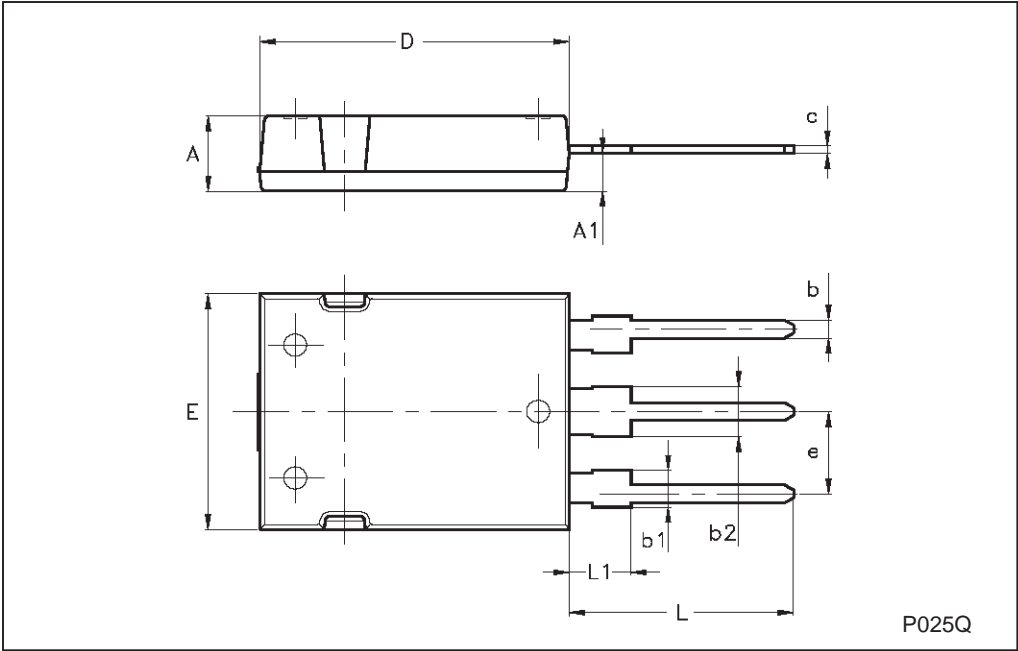


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



Max247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.70		5.30			
A1	2.20		2.60			
b	1.00		1.40			
b1	2.00		2.40			
b2	3.00		3.40			
c	0.40		0.80			
D	19.70		20.30			
e	5.35		5.55			
E	15.30		15.90			
L	14.20		15.20			
L1	3.70		4.30			



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